



PMZB550UNE

30 V, N-channel Trench MOSFET
25 March 2015

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Ultra thin package profile of 0.37 mm height

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_J = 25\text{ }^{\circ}\text{C}$		-	-	30	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	-	590	mA
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 590\text{ mA}; T_J = 25\text{ }^{\circ}\text{C}$		-	550	670	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

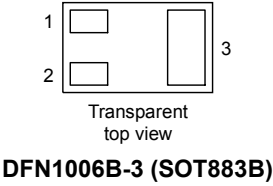
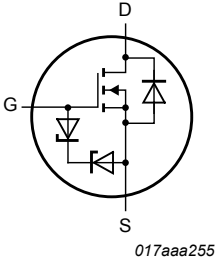


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 Transparent top view DFN1006B-3 (SOT883B)	 017aaa255
2	S	source		
3	D	drain		

6. Ordering information

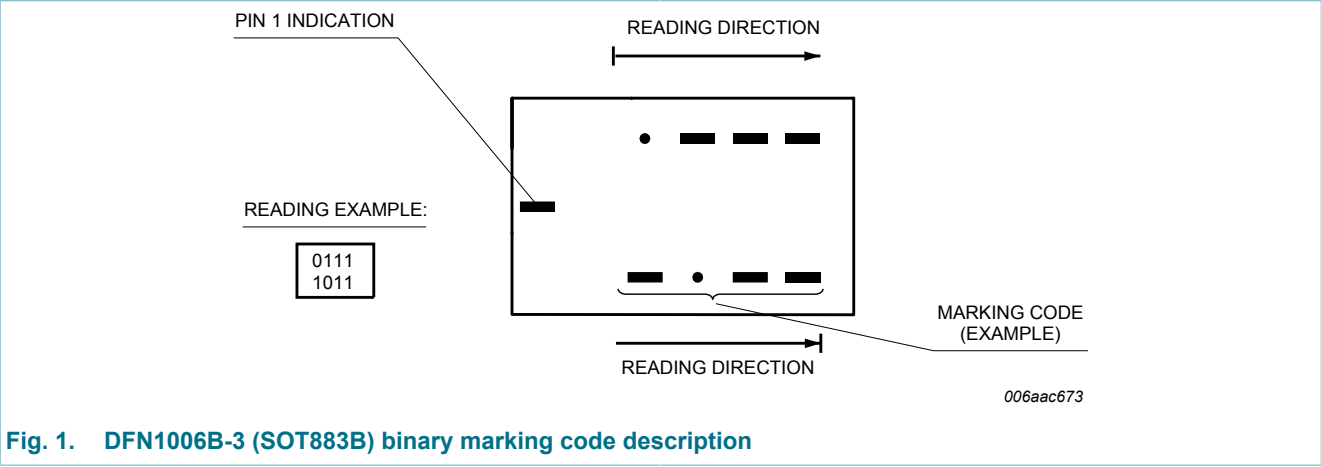
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZB550UNE	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZB550UNE	0101 0101

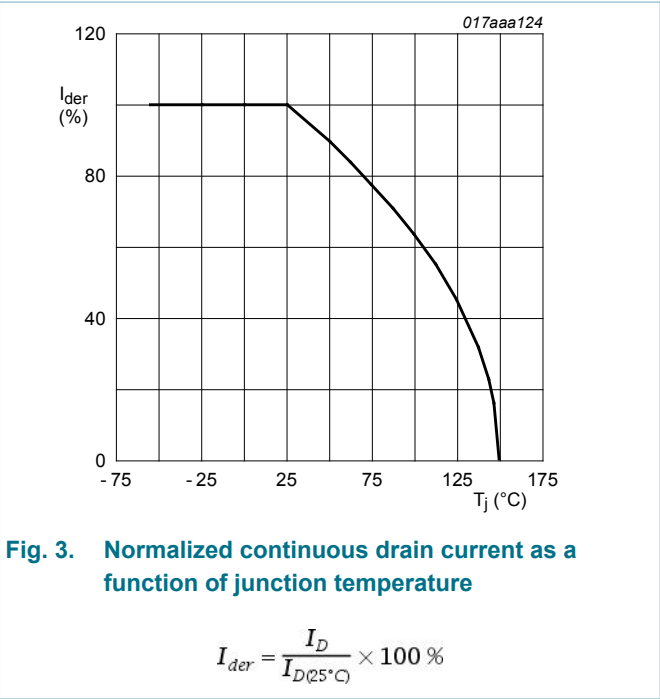
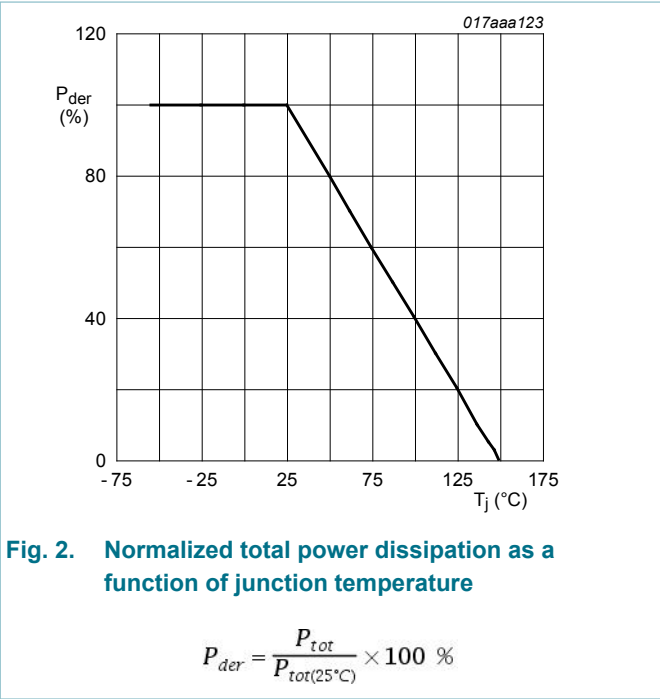


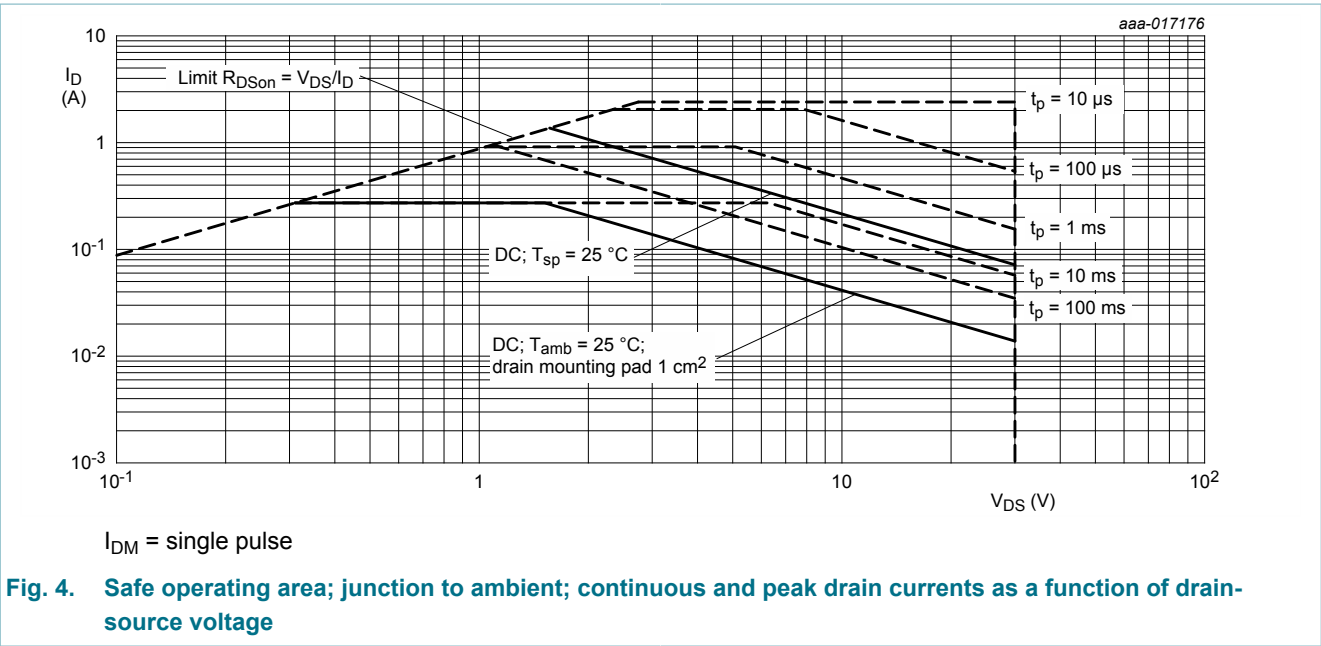
8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	590	mA
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	370	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	2.3	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T _{sp} = 25 °C		-	1670	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	380	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



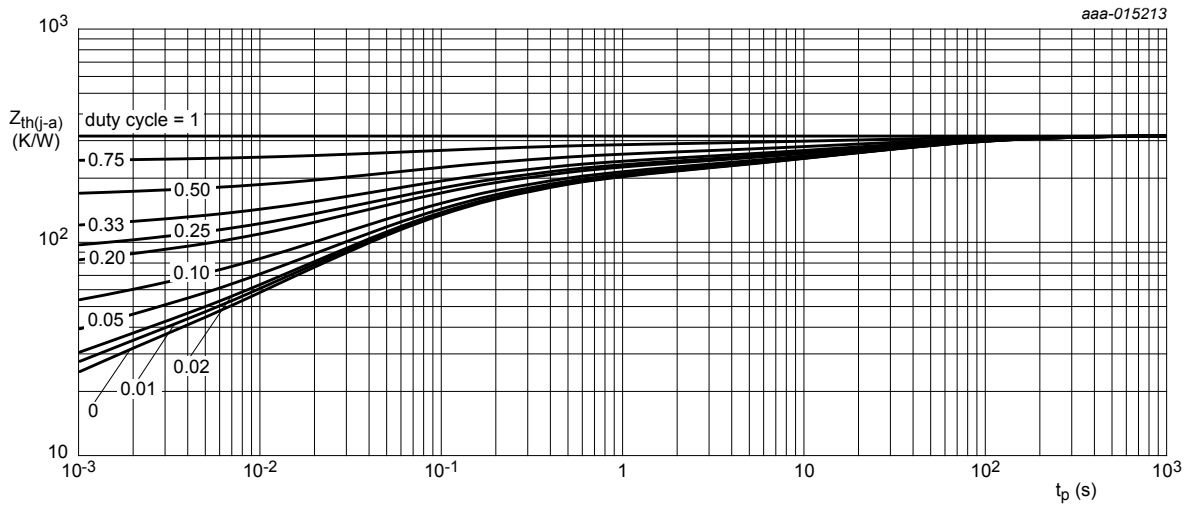


9. Thermal characteristics

Table 6. Thermal characteristics

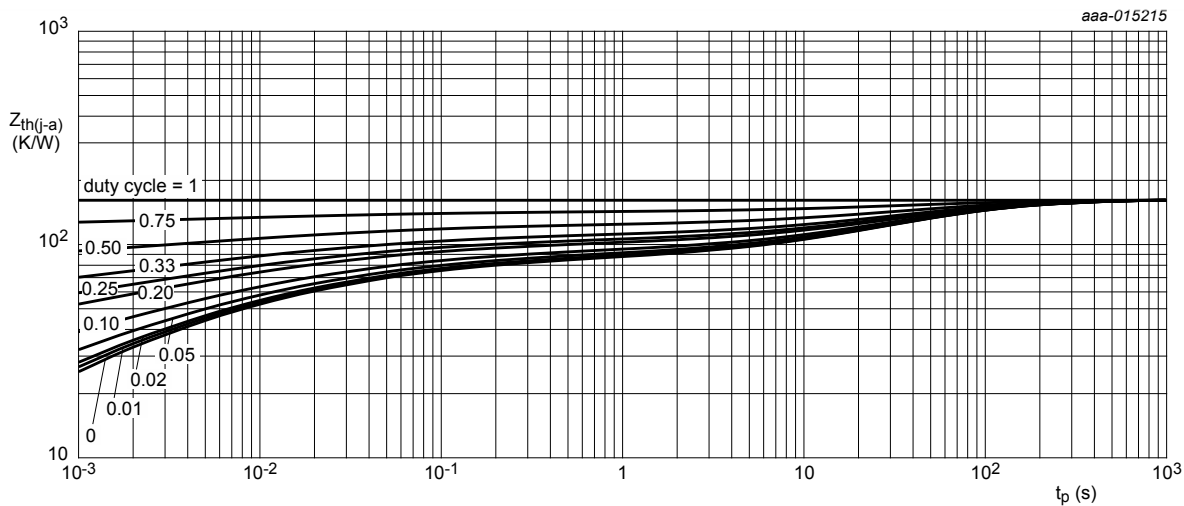
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	350	405	K/W
			[2]	-	270	310	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	65	75	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		0.45	0.7	0.95	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C		-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	5	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	-5	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C		-	-	1	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C		-	-	-1	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C		-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 590 mA; T _j = 25 °C		-	550	670	mΩ
		V _{GS} = 4.5 V; I _D = 590 mA; T _j = 150 °C		-	960	1170	mΩ
		V _{GS} = 2.5 V; I _D = 590 mA; T _j = 25 °C		-	660	900	mΩ
		V _{GS} = 1.8 V; I _D = 80 mA; T _j = 25 °C		-	770	1120	mΩ
		V _{GS} = 1.5 V; I _D = 10 mA; T _j = 25 °C		-	890	1500	mΩ
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 590 mA; T _j = 25 °C		-	600	-	mS
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 590 mA; V _{GS} = 4.5 V; T _j = 25 °C		-	0.6	1.1	nC
Q _{GS}	gate-source charge			-	0.1	-	nC
Q _{GD}	gate-drain charge			-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	30.3	-	pF
C _{oss}	output capacitance			-	5.8	-	pF
C _{rss}	reverse transfer capacitance			-	4.2	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 590 mA; V _{GS} = 4.5 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	4	-	ns
t _r	rise time			-	7	-	ns
t _{d(off)}	turn-off delay time			-	12	-	ns
t _f	fall time			-	3	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 380 mA; V _{GS} = 0 V; T _j = 25 °C		-	0.86	1.2	V

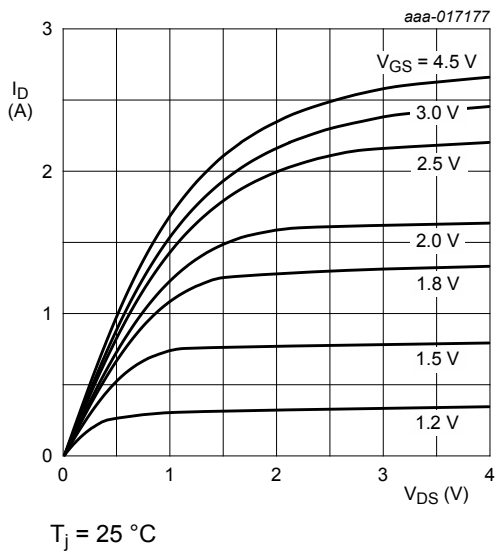


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

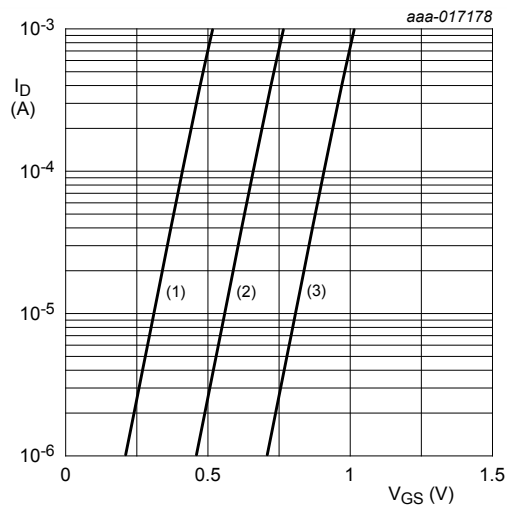


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

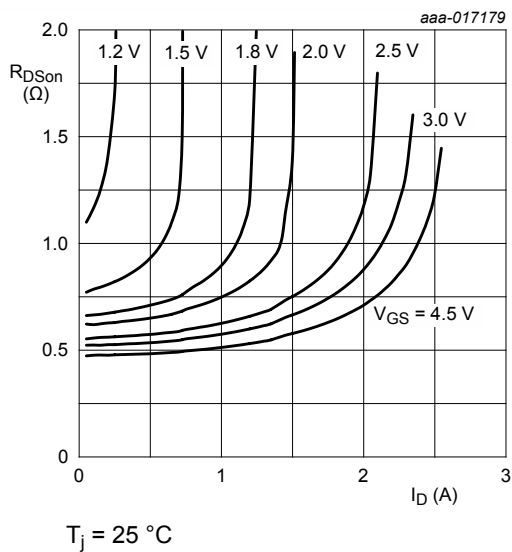


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

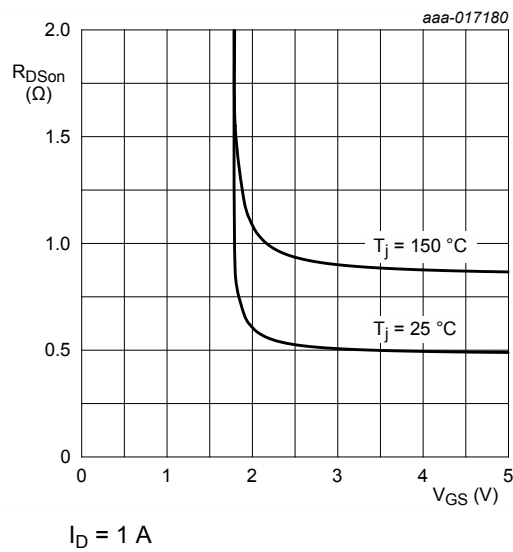


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

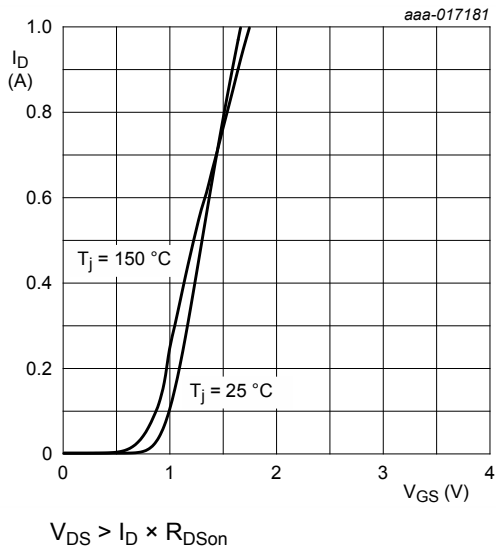


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

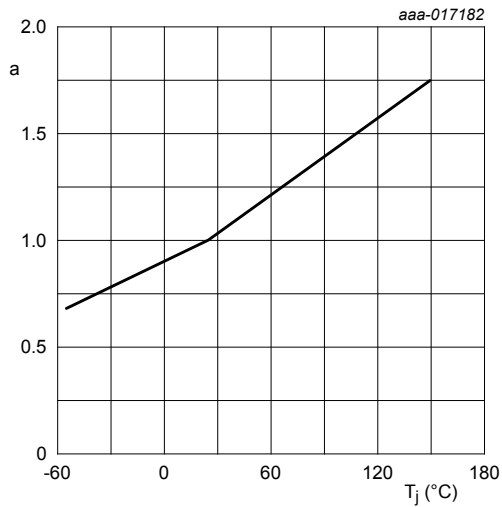


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DS(on)}}{R_{DS(on)25^{\circ}C}}$$

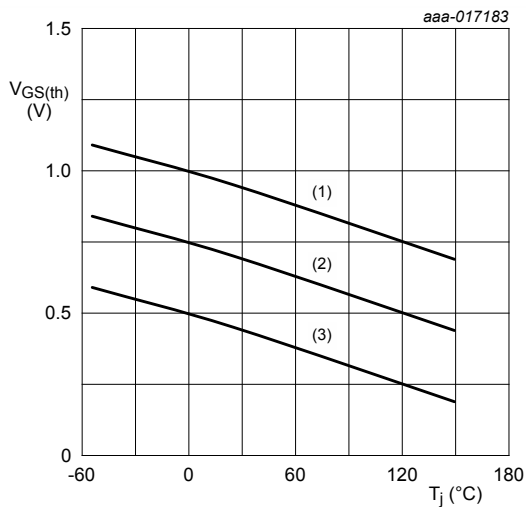


Fig. 13. Gate-source threshold voltage as a function of junction temperature

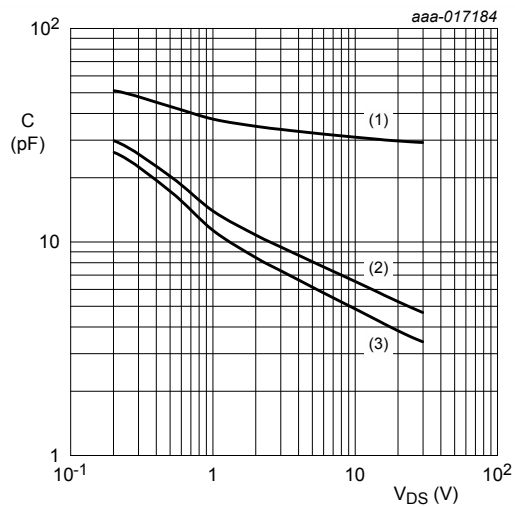


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

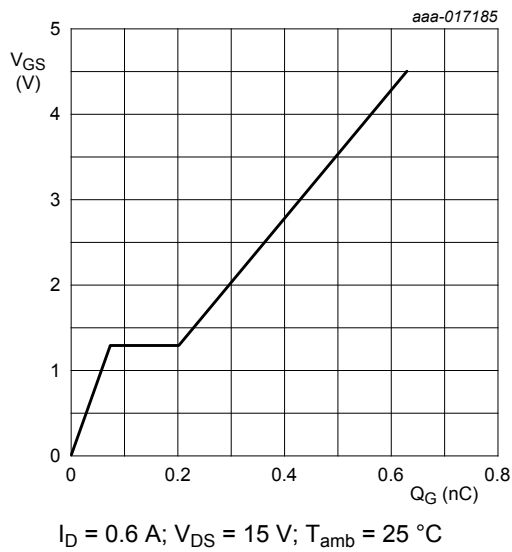


Fig. 15. Gate-source voltage as a function of gate charge; typical values

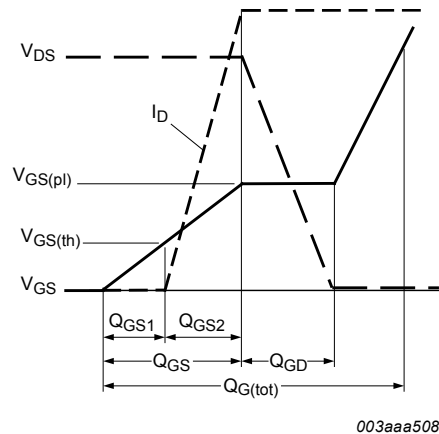


Fig. 16. Gate charge waveform definitions

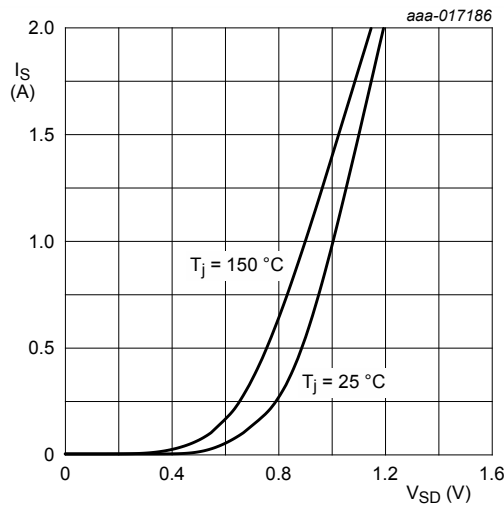


Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

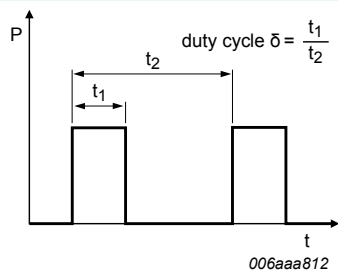


Fig. 18. Duty cycle definition

12. Package outline

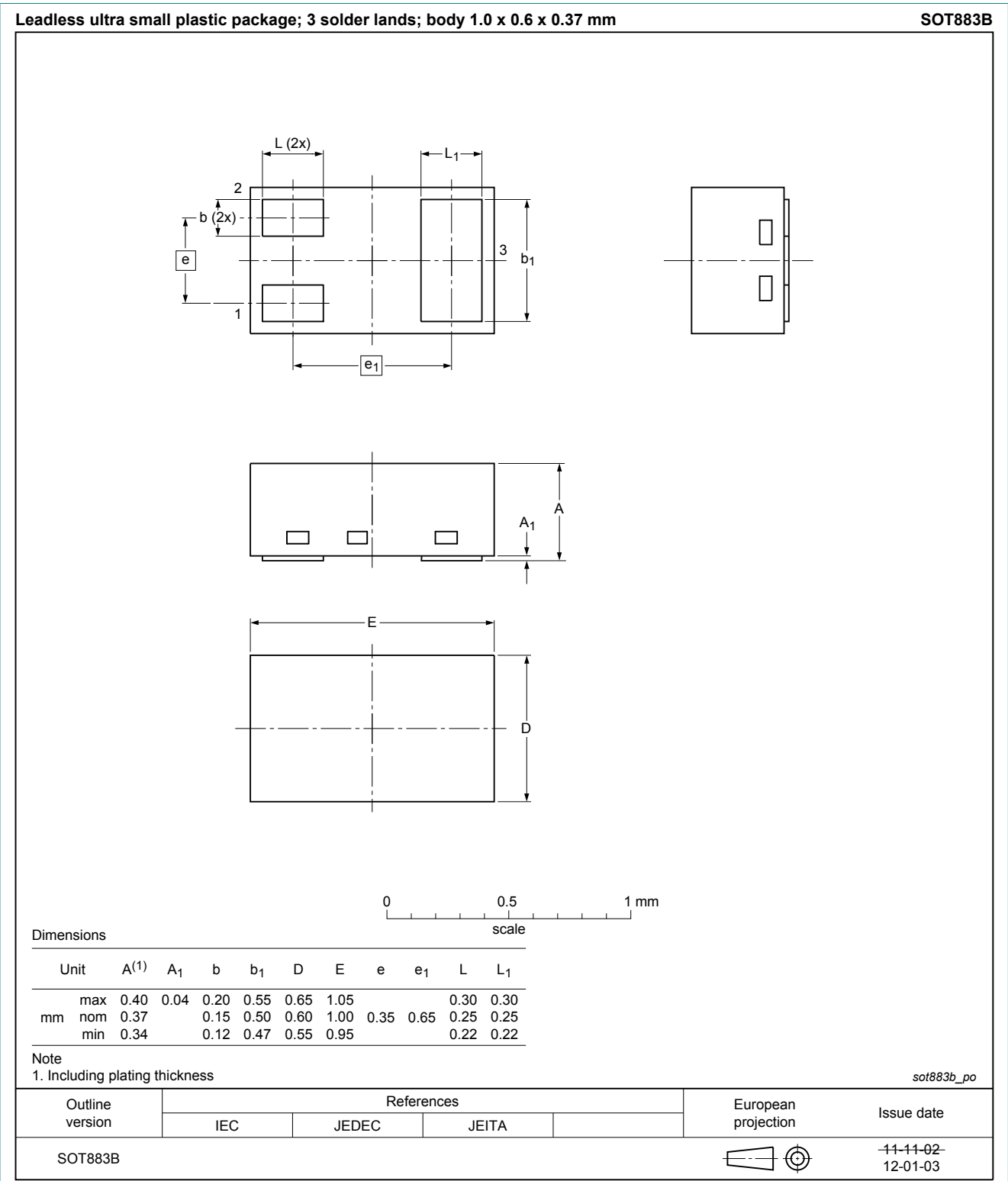
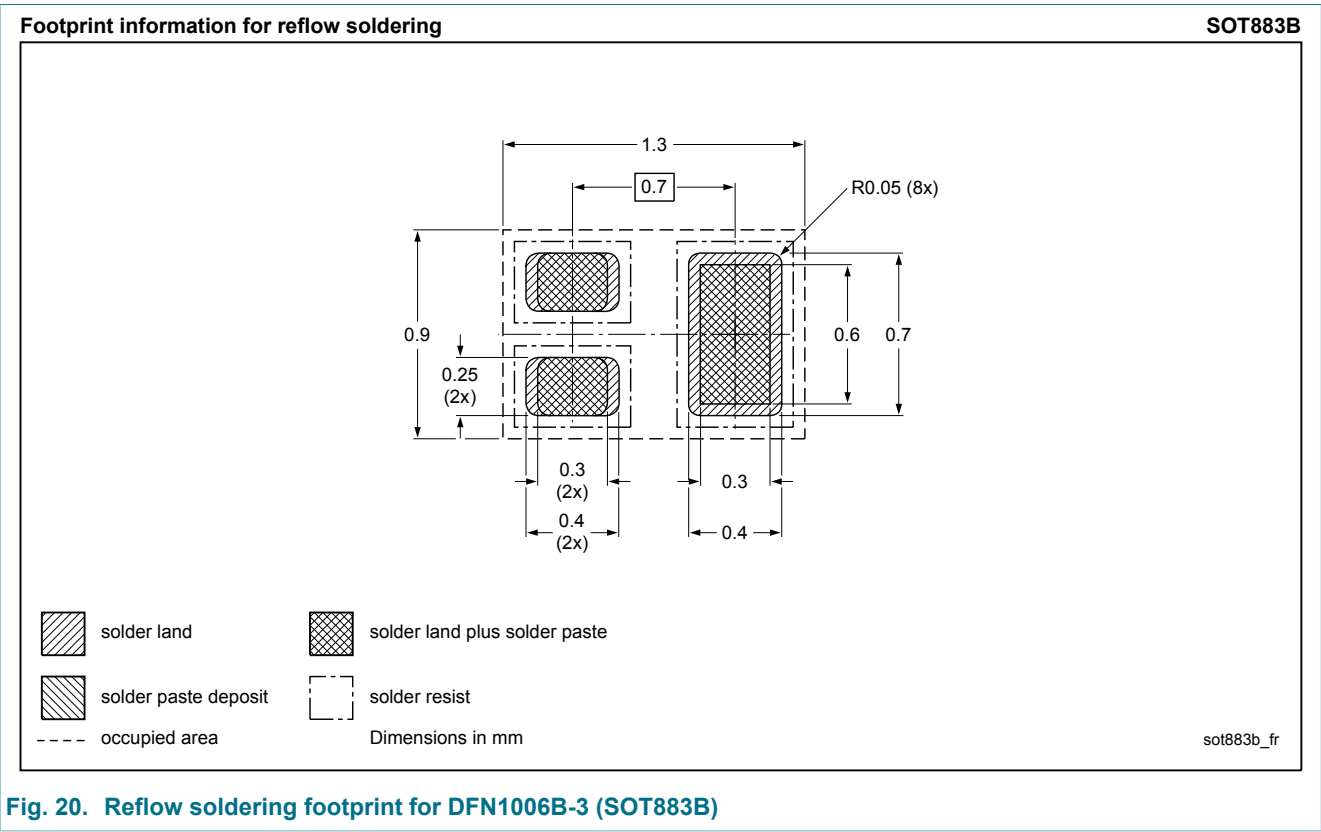


Fig. 19. Package outline DFN1006B-3 (SOT883B)

13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB550UNE v.1	20150325	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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